

L A Coldren

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

155
papers

5,971
citations

41
h-index

72
g-index

164
ext. papers

6,660
ext. citations

3.6
avg, IF

4.95
L-index

#	Paper	IF	Citations
155	. <i>IEEE Photonics Journal</i> , 2017 , 9, 1-14	1.8	12
154	Fully integrated hybrid silicon two dimensional beam scanner. <i>Optics Express</i> , 2015 , 23, 5861-74	3.3	182
153	Single-chip dual-pumped SOA-based phase-sensitive amplifier at 1550nm 2015 ,		2
152	30 Gbps bottom-emitting 1060 nm VCSEL 2014 ,		1
151	Fully integrated hybrid silicon free-space beam steering source with 32-channel phased array 2014 ,		8
150	Hybrid silicon free-space source with integrated beam steering 2013 ,		1
149	. <i>Journal of Lightwave Technology</i> , 2013 , 31, 2244-2253	4	31
148	Two-Dimensional Optical Beam Steering With InP-Based Photonic Integrated Circuits. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 6100212-6100212	3.8	48
147	Hybrid III/V silicon photonic source with integrated 1D free-space beam steering. <i>Optics Letters</i> , 2012 , 37, 4257-9	3	43
146	Two-dimensional free-space beam steering with an optical phased array on silicon-on-insulator. <i>Optics Express</i> , 2011 , 19, 21595-604	3.3	221
145	Externally mode-matched cavity quantum electrodynamics with charge-tunable quantum dots. <i>Physical Review Letters</i> , 2009 , 102, 097403	7.4	63
144	Picosecond coherent optical manipulation of a single electron spin in a quantum dot. <i>Science</i> , 2008 , 320, 349-52	33.3	402
143	Optically detected coherent spin dynamics of a single electron in a quantum dot. <i>Nature Physics</i> , 2007 , 3, 770-773	16.2	112
142	Introduction to the Issue on Semiconductor Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2007 , 13, 1043-1045	3.8	
141	Fabrication and molecular beam epitaxy regrowth of first-order, high contrast AlGaAs/GaAs gratings. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 1559		1
140	Nondestructive optical measurements of a single electron spin in a quantum dot. <i>Science</i> , 2006 , 314, 1916-20	33.3	151
139	Terahertz-optical mixing in undoped and doped GaAs quantum wells: From excitonic to electronic intersubband transitions. <i>Physical Review B</i> , 2005 , 72,	3.3	11

138	High-differential-quantum-efficiency, long-wavelength vertical-cavity lasers using five-stage bipolar-cascade active regions. <i>Applied Physics Letters</i> , 2005 , 86, 211104	3-4	7
137	Terahertz electro-optic wavelength conversion in GaAs quantum wells: Improved efficiency and room-temperature operation. <i>Applied Physics Letters</i> , 2004 , 84, 840-842	3-4	28
136	A monolithic diode laser chemical sensor with a quasi-symmetrical sensing waveguide for improved sensitivity. <i>Applied Physics Letters</i> , 2004 , 85, 320-322	3-4	4
135	Terahertz optical mixing in biased GaAs single quantum wells. <i>Physical Review B</i> , 2004 , 70,	3-3	13
134	Selectively etched tunnel junction for lateral current and optical confinement in InP-based vertical cavity lasers. <i>Journal of Electronic Materials</i> , 2004 , 33, 118-122	1-9	6
133	Strong-field terahertz optical mixing in excitons. <i>Physical Review B</i> , 2003 , 67,	3-3	16
132	Al _{0.95} Ga _{0.05} As _{0.56} Sb _{0.44} for lateral oxide-confinement layer in InP-based devices. <i>Applied Physics Letters</i> , 2003 , 82, 1329-1331	3-4	6
131	Molecular-beam epitaxy growth of high-quality active regions with strained In _x Ga _{1-x} As quantum wells and lattice-matched Al _x Ga _{1-x} In(1-x)As barriers using submonolayer superlattices. <i>Applied Physics Letters</i> , 2002 , 80, 3509-3511	3-4	14
130	Voltage-controlled wavelength conversion by terahertz electro-optic modulation in double quantum wells. <i>Applied Physics Letters</i> , 2002 , 81, 1564-1566	3-4	27
129	Chemical Mechanical Polishing of Gallium Nitride. <i>Electrochemical and Solid-State Letters</i> , 2002 , 5, G61		54
128	Rate equations of vertical-cavity semiconductor optical amplifiers. <i>Applied Physics Letters</i> , 2002 , 80, 3057-3059	3-4	3
127	88 °C, continuous-wave operation of apertured, intracavity contacted, 1.55 μ m vertical-cavity surface-emitting lasers. <i>Applied Physics Letters</i> , 2001 , 78, 1337-1339	3-4	36
126	Increased lateral oxidation rates of AlInAs on InP using short-period superlattices. <i>Journal of Electronic Materials</i> , 2000 , 29, 1100-1104	1-9	4
125	Molecular beam epitaxial growth of monolithic 1.55 μ m vertical cavity surface emitting lasers with AlGaAsSb/AlAsSb Bragg mirrors. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000 , 18, 1601		8
124	Improved characteristics of InGaN multiple-quantum-well laser diodes grown on laterally epitaxially overgrown GaN on sapphire. <i>Applied Physics Letters</i> , 2000 , 76, 529-531	3-4	55
123	Near-room-temperature continuous-wave operation of multiple-active-region 1.55 μ m vertical-cavity lasers with high differential efficiency. <i>Applied Physics Letters</i> , 2000 , 77, 3137-3139	3-4	32
122	Enhanced wavelength tuning of an InGaAsP-InP laser with a thermal-strain-magnifying trench. <i>Applied Physics Letters</i> , 2000 , 77, 2629-2631	3-4	6
121	Measured and calculated radiative lifetime and optical absorption of In _x Ga _{1-x} N/GaN quantum structures. <i>Physical Review B</i> , 2000 , 61, 10994-11008	3-3	128

120	Individually optimized bottom-emitting vertical-cavity lasers and bottom-illuminated resonant photodetectors sharing the same epitaxial structure. <i>Journal of Optics</i> , 1999 , 1, 317-319		2
119	Epitaxially-stacked multiple-active-region 1.55 μ m lasers for increased differential efficiency. <i>Applied Physics Letters</i> , 1999 , 74, 3251-3253	3-4	41
118	Effect of AlGaIn/GaN Strained Layer Superlattice Period on InGaIn MQW Laser Diodes. <i>Physica Status Solidi A</i> , 1999 , 176, 59-62		8
117	Design parameters for lateral carrier confinement in quantum-dot lasers. <i>Applied Physics Letters</i> , 1999 , 74, 2752-2754	3-4	31
116	Indium tin oxide contacts to gallium nitride optoelectronic devices. <i>Applied Physics Letters</i> , 1999 , 74, 3930-3932	3-4	187
115	Effective band gap inhomogeneity and piezoelectric field in InGaIn/GaN multiquantum well structures. <i>Applied Physics Letters</i> , 1998 , 73, 2006-2008	3-4	380
114	Minimum temperature sensitivity of 1.55 μ m vertical-cavity lasers at 30 nm gain offset. <i>Applied Physics Letters</i> , 1998 , 72, 1814-1816	3-4	62
113	Parallel free-space optical interconnect based on arrays of vertical-cavity lasers and detectors with monolithic microlenses. <i>Applied Optics</i> , 1998 , 37, 2811-21	1-7	38
112	Measurement of the AlGaInAs/AlGaAs conduction-band offset using ballistic electron emission spectroscopy. <i>Applied Physics Letters</i> , 1998 , 73, 3271-3272	3-4	3
111	Measurement of gain current relations for InGaIn multiple quantum wells. <i>Applied Physics Letters</i> , 1998 , 73, 3887-3889	3-4	9
110	Catastrophic optical damage in GaInN multiple quantum wells. <i>Applied Physics Letters</i> , 1998 , 72, 3267-3269		7
109	Effects of Si-doping in the barriers of InGaIn multiquantum well purplish-blue laser diodes. <i>Applied Physics Letters</i> , 1998 , 73, 496-498	3-4	63
108	Technique for integration of vertical cavity lasers and resonant photodetectors. <i>Applied Physics Letters</i> , 1998 , 73, 1-3	3-4	40
107	Surface energy model for the thickness dependence of the lateral oxidation of AlAs. <i>Journal of Applied Physics</i> , 1997 , 82, 2277-2280	2-5	46
106	Reconfigurable optical properties in InGaIn/GaN quantum wells. <i>Applied Physics Letters</i> , 1997 , 71, 1455-1457	3-4	11
105	Coupled-cavity resonant photodetectors for high-performance wavelength demultiplexing applications. <i>Applied Physics Letters</i> , 1997 , 71, 178-180	3-4	9
104	Gain spectroscopy on InGaIn/GaN quantum well diodes. <i>Applied Physics Letters</i> , 1997 , 70, 2580-2582	3-4	51
103	Reduced lateral carrier diffusion for improved miniature semiconductor lasers. <i>Journal of Applied Physics</i> , 1997 , 81, 3377-3381	2-5	16

102	Resonant-cavity InGaAs/InAlGaAs/InP photodetector arrays for wavelength demultiplexing applications. <i>Applied Physics Letters</i> , 1997 , 70, 2347-2349	3.4	16
101	Photoluminescence characteristics of GaN/InGaN/GaN quantum wells. <i>Journal of Electronic Materials</i> , 1997 , 26, 325-329	1.9	2
100	Growth and characterization of bulk InGaN films and quantum wells. <i>Applied Physics Letters</i> , 1996 , 68, 3147-3149	3.4	142
99	Vertical-cavity surface-emitting lasers for free-space interconnects 1996 , 10284, 8		
98	Molecular beam epitaxial growth of strained AlGaInAs multi-quantum well lasers on InP. <i>Journal of Electronic Materials</i> , 1996 , 25, 948-954	1.9	3
97	InP-based multiple quantum well structures grown with tertiarybutylarsine (TBA) and tertiarybutylphosphine (TBP): Effects of growth interruptions on structural and optical properties. <i>Journal of Electronic Materials</i> , 1996 , 25, 965-971	1.9	2
96	Estimation of scattering losses in dielectrically apertured vertical cavity lasers. <i>Applied Physics Letters</i> , 1996 , 68, 1757-1759	3.4	57
95	Dielectric apertures as intracavity lenses in vertical-cavity lasers. <i>Applied Physics Letters</i> , 1996 , 68, 313-315	3.4	32
94	Effects of surface recombination on carrier distributions and device characteristics. <i>Journal of Applied Physics</i> , 1995 , 78, 3208-3215	2.5	3
93	Calibrated intensity noise measurements in microcavity laser diodes. <i>Applied Physics Letters</i> , 1995 , 67, 3697-3699	3.4	21
92	Intensity noise and facet correlation in Fabry-Pérot laser diodes with low facet reflectivities. <i>Applied Physics Letters</i> , 1995 , 66, 3419-3421	3.4	3
91	Temperature-dependent threshold and modulation characteristics in InGaAs/GaAs quantum-well ridge-waveguide lasers. <i>Applied Physics Letters</i> , 1995 , 66, 2040-2042	3.4	18
90	Surface migration induced self-aligned InAs islands grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 1995 , 66, 1620-1622	3.4	162
89	Low regrowth interface recombination rates in InGaAs/AlGaAs buried ridge lasers fabricated by in situ processing. <i>Applied Physics Letters</i> , 1995 , 66, 1966-1968	3.4	14
88	Evaluating the effects of optical and carrier losses in etched-post vertical cavity lasers. <i>Journal of Applied Physics</i> , 1995 , 78, 5871-5875	2.5	35
87	Many body effects in the temperature dependence of threshold in a vertical-cavity surface-emitting laser. <i>Applied Physics Letters</i> , 1995 , 66, 2460-2462	3.4	20
86	High modulation efficiency of intracavity contacted vertical cavity lasers. <i>Applied Physics Letters</i> , 1994 , 65, 1483-1485	3.4	46
85	Lateral carrier diffusion and surface recombination in InGaAs/AlGaAs quantum-well ridge-waveguide lasers. <i>Journal of Applied Physics</i> , 1994 , 76, 4479-4487	2.5	61

84	High-efficiency and low-threshold InGaAs/AlGaAs quantum-well lasers. <i>Journal of Applied Physics</i> , 1994 , 76, 3932-3934	2.5	23
83	Tertiarybutylarsine and tertiarybutylphosphine for the MOCVD growth of low threshold 1.55 μm In _x Ga _{1-x} As/InP quantum-well lasers. <i>Journal of Electronic Materials</i> , 1994 , 23, 87-91	1.9	21
82	Effects of Hydrogen on Chlorine Radical-Beam Ion-Beam Etching of Al _x Ga _{1-x} As with Varying Mole Fraction. <i>Journal of the Electrochemical Society</i> , 1993 , 140, 1802-1804	3.9	2
81	Photonic integrated tunable receivers with optical preamplifiers for direct detection. <i>Applied Physics Letters</i> , 1993 , 63, 880-882	3.4	11
80	Band-gap engineered digital alloy interfaces for lower resistance vertical-cavity surface-emitting lasers. <i>Applied Physics Letters</i> , 1993 , 63, 3411-3413	3.4	78
79	Modeling the current to light characteristics of index-guided vertical-cavity surface-emitting lasers. <i>Applied Physics Letters</i> , 1993 , 62, 1050-1052	3.4	24
78	Optical gain anisotropy in serpentine superlattice nanowire-array lasers. <i>Applied Physics Letters</i> , 1993 , 63, 2015-2017	3.4	17
77	Large and small signal dynamics of vertical cavity surface emitting lasers. <i>Applied Physics Letters</i> , 1993 , 62, 325-327	3.4	75
76	Design, fabrication and characterization of high-speed asymmetric Fabry-Perot modulators for optical interconnect applications. <i>Optical and Quantum Electronics</i> , 1993 , 25, S885-S898	2.4	12
75	Guide/antiguide optical intensity modulator. <i>Optical and Quantum Electronics</i> , 1993 , 25, S899-S915	2.4	
74	Characterization of geometric effects for the guide/antiguide intensity modulator. <i>Journal of Applied Physics</i> , 1992 , 72, 4455-4457	2.5	
73	Effect of layer thickness variations on the performance of asymmetric Fabry-Perot reflection modulators. <i>Journal of Applied Physics</i> , 1992 , 72, 855-860	2.5	20
72	Analysis and optimization of quantum-well thickness for GaAs/AlGaAs and InGaAs/GaAs/AlGaAs quantum-well lasers. <i>Journal of Applied Physics</i> , 1992 , 72, 5047-5054	2.5	6
71	Demonstration of broadband tunability in a semiconductor laser using sampled gratings. <i>Applied Physics Letters</i> , 1992 , 60, 2321-2323	3.4	61
70	Efficient vertical-cavity lasers. <i>Optical and Quantum Electronics</i> , 1992 , 24, S105-S119	2.4	24
69	High Performance Quantum Well Asymmetric Fabry-Perot Reflection Modulators: Effect of Layer Thickness Variations. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 240, 609		0
68	High-contrast, large optical bandwidth field-induced guide/antiguide modulator. <i>Applied Physics Letters</i> , 1991 , 58, 2211-2213	3.4	8
67	Observation of anomalously large blue shift of the heavy-hole photocurrent peak and optical bistability in narrow asymmetric coupled quantum wells. <i>Applied Physics Letters</i> , 1991 , 59, 1025-1027	3.4	13

66	Analysis and optimization of graded-index separate-confinement heterostructure waveguides for quantum well lasers. <i>Journal of Applied Physics</i> , 1991 , 69, 2857-2861	2.5	16
65	Theoretical gain in compressive and tensile strained InGaAs/InGaAsP quantum wells. <i>Applied Physics Letters</i> , 1991 , 59, 588-590	3.4	37
64	Low-threshold high-efficiency high-yield impurity-induced layer disordering laser by self-aligned Si-Zn diffusion. <i>Applied Physics Letters</i> , 1990 , 57, 2534-2536	3.4	13
63	Normally-off high-contrast asymmetric FabryPerot reflection modulator using WannierStark localization in a superlattice. <i>Applied Physics Letters</i> , 1990 , 56, 1886-1888	3.4	47
62	Simultaneous gain and phase-shift enhancements in periodic gain structures. <i>Journal of Applied Physics</i> , 1990 , 67, 4387-4389	2.5	3
61	Asymmetric FabryPerot reflection modulators using red- and blue-shifted electroabsorption effects. <i>Journal of Applied Physics</i> , 1990 , 68, 875-877	2.5	3
60	Generation of picosecond pulses with a gain-switched GaAs surface-emitting laser. <i>Applied Physics Letters</i> , 1990 , 57, 963-965	3.4	23
59	Self-electro-optic device based on a superlattice asymmetric FabryPerot modulator with an on/off ratio ?100:1. <i>Applied Physics Letters</i> , 1990 , 57, 1345-1347	3.4	59
58	Effect of temperature on the operating characteristics of asymmetric FabryPerot reflection modulators. <i>Applied Physics Letters</i> , 1990 , 57, 267-269	3.4	14
57	Transverse modulators with a record reflection change of >20%/V using asymmetric FabryPerot structures. <i>Applied Physics Letters</i> , 1990 , 56, 1626-1628	3.4	31
56	GaAs/AlGaAs multiple quantum well field-induced optical waveguide. <i>Applied Physics Letters</i> , 1990 , 57, 114-116	3.4	17
55	Theoretical gain in strained InGaAs/AlGaAs quantum wells including valence-band mixing effects. <i>Applied Physics Letters</i> , 1990 , 57, 2835-2837	3.4	116
54	Comparison of quantum-confined Stark effect in interdiffused and abrupt GaAs/AlGaAs quantum wells. <i>Applied Physics Letters</i> , 1989 , 55, 2526-2528	3.4	2
53	Spontaneous growth of coherent tilted superlattice on vicinal (100) GaAs substrates. <i>Applied Physics Letters</i> , 1989 , 54, 1690-1692	3.4	100
52	Disordering of GaAs/AlGaAs multiple quantum well structures by thermal annealing for monolithic integration of laser and phase modulator. <i>Applied Physics Letters</i> , 1989 , 55, 672-674	3.4	30
51	Tight-binding analysis on exciton binding energy in field-induced Stark-localized superlattices. <i>Applied Physics Letters</i> , 1989 , 55, 2002-2004	3.4	19
50	Optical anisotropy in a quantum-well-wire array with two-dimensional quantum confinement. <i>Physical Review Letters</i> , 1989 , 62, 466-469	7.4	354
49	Wide-bandwidth, high-efficiency reflection modulators using an unbalanced FabryPerot structure. <i>Applied Physics Letters</i> , 1989 , 55, 1946-1948	3.4	21

48	Room-temperature two-dimension exciton exchange and blue shift of absorption edge in GaAs/AlGaAs superlattices under an electric field. <i>Applied Physics Letters</i> , 1989 , 54, 1549-1551	3-4	27
47	High-efficiency TEM00 continuous-wave (Al,Ga)As epitaxial surface-emitting lasers and effect of half-wave periodic gain. <i>Applied Physics Letters</i> , 1989 , 54, 1209-1211	3-4	36
46	Optically addressed spatial light modulators by MBE-grown nipi MQW structures. <i>Applied Optics</i> , 1989 , 28, 4801-7	1.7	14
45	Optically controlled reflection modulator using GaAs-AlGaAs n-i-p-i/multiple-quantum-well structures. <i>Optics Letters</i> , 1989 , 14, 230-2	3	11
44	Relating the chirp parameter to the number of quantum wells in GaAs/AlGaAs waveguide modulators. <i>Applied Physics Letters</i> , 1989 , 55, 718-720	3-4	5
43	Compound-Cavity Lasers For Medium Range Lidar Applications 1989 ,		2
42	Extremely wide modulation bandwidth in a low threshold current strained quantum well laser. <i>Applied Physics Letters</i> , 1988 , 53, 1378-1380	3-4	185
41	Use of independently controlled Cl radical and Ar ion beams for anisotropic chemically enhanced etching of GaAs. <i>Applied Physics Letters</i> , 1988 , 53, 2308-2310	3-4	7
40	Impurity-induced-disordered phase modulators in AlGaAs/GaAs quantum well and double-heterostructure waveguides. <i>Applied Physics Letters</i> , 1988 , 53, 728-730	3-4	6
39	Real-time technique for the characterization of tunable single-frequency lasers. <i>Applied Physics Letters</i> , 1988 , 52, 2217-2219	3-4	
38	Self-aligned Si-Zn diffusion into GaAs and AlGaAs. <i>Journal of Applied Physics</i> , 1988 , 64, 1855-1858	2.5	6
37	Radical beam/ion beam etching of GaAs. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1988 , 6, 1885		13
36	Electrically tunable FabryPerot mirror using multiple quantum well index modulation. <i>Applied Physics Letters</i> , 1988 , 53, 637-639	3-4	42
35	Dry Etching and Impurity Diffusion for Integrated Optoelectronics. <i>Materials Research Society Symposia Proceedings</i> , 1988 , 126, 237		3
34	Design of optimized high-speed depletion-edge-translation optical waveguide modulators in III-V semiconductors. <i>Applied Physics Letters</i> , 1987 , 51, 792-794	3-4	17
33	Behavior of SiNx films as masks for Zn diffusion. <i>Journal of Applied Physics</i> , 1987 , 62, 828-831	2.5	10
32	Contribution of the band-filling effect to the effective refractive-index change in double-heterostructure GaAs/AlGaAs phase modulators. <i>Journal of Applied Physics</i> , 1987 , 62, 4548-4553	2.5	23
31	Electrorefraction in GaAs and InGaAsP and its application to phase modulators. <i>Journal of Applied Physics</i> , 1987 , 61, 2430-2433	2.5	56

30	Silicon diffusion into Al _x Ga _{1-x} As (x=0.4) from a sputtered silicon film. <i>Applied Physics Letters</i> , 1987 , 50, 265-266	3.4	9
29	Sputtered silicon as a new etching mask for GaAs devices. <i>Journal of Applied Physics</i> , 1986 , 60, 1218-1220.	3.5	2
28	Continuous tunability in three-terminal coupled-cavity lasers. <i>Applied Physics Letters</i> , 1986 , 48, 1190-1193.	3.4	11
27	Highly efficient waveguide phase modulator for integrated optoelectronics. <i>Applied Physics Letters</i> , 1986 , 48, 1243-1245	3.4	43
26	Reduced dynamic linewidth in three-terminal two-section diode lasers. <i>Applied Physics Letters</i> , 1985 , 46, 125-127	3.4	10
25	Etched-groove coupled-cavity vapor-phase-transported window lasers at 1.55 μ m. <i>Applied Physics Letters</i> , 1985 , 46, 5-7	3.4	7
24	Optimum coupling junction and cavity lengths for coupled-cavity semiconductor lasers. <i>Journal of Applied Physics</i> , 1985 , 57, 740-754	2.5	16
23	Continuous operation of monolithic dynamic-single-mode coupled-cavity lasers. <i>Applied Physics Letters</i> , 1984 , 44, 368-370	3.4	12
22	Optoelectronic properties of coupled cavity semiconductor lasers. <i>Applied Physics Letters</i> , 1984 , 44, 735-737	3.4	6
21	Stabilization and optimum biasing of dynamic-single-mode coupled-cavity lasers. <i>Applied Physics Letters</i> , 1984 , 44, 169-171	3.4	15
20	Cleaved-coupled-cavity lasers with large cavity length ratios for enhanced stability. <i>Applied Physics Letters</i> , 1984 , 44, 821-823	3.4	15
19	On the Formation of Planar-Etched Facets in GaInAsP / InP Double Heterostructures. <i>Journal of the Electrochemical Society</i> , 1983 , 130, 1918-1926	3.9	32
18	Single-mode operation of coupled-cavity GaInAsP/InP semiconductor lasers. <i>Applied Physics Letters</i> , 1983 , 42, 6-8	3.4	58
17	Analysis of multielement semiconductor lasers. <i>Journal of Applied Physics</i> , 1983 , 54, 2962-2969	2.5	53
16	Directional reactive-ion-etching of InP with Cl ₂ containing gases. <i>Journal of Vacuum Science and Technology</i> , 1981 , 19, 225-230		45
15	Monolithic two-section GaInAsP/InP active-optical-resonator devices formed by reactive ion etching. <i>Applied Physics Letters</i> , 1981 , 38, 315-317	3.4	119
14	Reactive ion beam etching of InP with Cl ₂ . <i>Applied Physics Letters</i> , 1981 , 38, 264-266	3.4	56
13	GaInAsP/InP stripe-geometry laser with a reactive-ion-etched facet. <i>Applied Physics Letters</i> , 1980 , 37, 681-683	3.4	95

12	Directional reactive ion etching at oblique angles. <i>Applied Physics Letters</i> , 1980 , 36, 583-585	3-4	57
11	Variable frequency SAW resonators on ferroelectric-ferroelastics. <i>Applied Physics Letters</i> , 1978 , 32, 129-131	3-4	10
10	Analog read-only memory using gadolinium molybdate. <i>Applied Physics Letters</i> , 1978 , 33, 373-375	3-4	9
9	Electronically variable delay using ferroelastic-ferroelectrics. <i>Applied Physics Letters</i> , 1977 , 30, 506-508	3-4	18
8	Zinc-oxide-on-silicon acoustically scanned imager with positive sensitivity and storage capabilities. <i>Applied Physics Letters</i> , 1975 , 27, 6-8	3-4	14
7	Acoustic waveguide with a cladged core geometry. <i>Applied Physics Letters</i> , 1975 , 26, 31-34	3-4	18
6	Zinc oxide on silicon memory cells scanned by acoustic surface waves. <i>Applied Physics Letters</i> , 1975 , 26, 137-139	3-4	11
5	Interior-surface acoustic waveguiding in capillaries. <i>Applied Physics Letters</i> , 1974 , 25, 324-326	3-4	9
4	Effect of bias field in a zinc-oxide-on-silicon acoustic convolver. <i>Applied Physics Letters</i> , 1974 , 25, 473-475	3-4	22
3	cw monolithic acoustic surface wave amplifier incorporated in a $\lambda/4$ waveguide. <i>Applied Physics Letters</i> , 1973 , 23, 117-118	3-4	17
2	MONOLITHIC ACOUSTIC SURFACE-WAVE AMPLIFIER. <i>Applied Physics Letters</i> , 1971 , 18, 317-319	3-4	34
1	TRAPPING MODEL FOR InSb THIN FILMS. <i>Applied Physics Letters</i> , 1971 , 18, 319-321	3-4	6